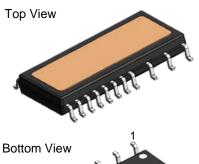
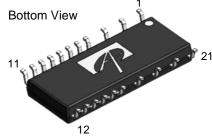


AIM7DT1AR60V3

Intelligent Power Module

External View





Size: 17.9 x 7.5 x 2.5 mm

Features

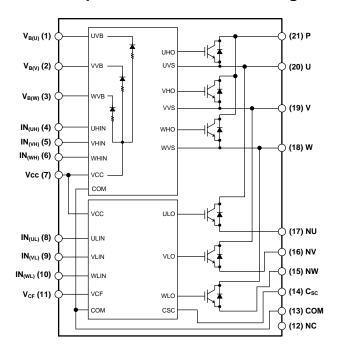
- 600V-1A
- · Fully functional 3-phase IGBT-IPM
- Reverse conducting IGBT with monolithic body diode
- DBC-embedded SMD type
- Wide input interface (3-18V) with schmitt-trigger input circuit
- Built-in bootstrap diodes with current-limiting resistor
- Control supply under-voltage lockout protection (UVLO)
- Over-temperature (OT) protection
- Short-circuit current protection (C_{SC})
- Controllable fault out signal (V_{CF}) corresponding to SC, UV, OT fault
- Isolation ratings of 1500Vrms/min

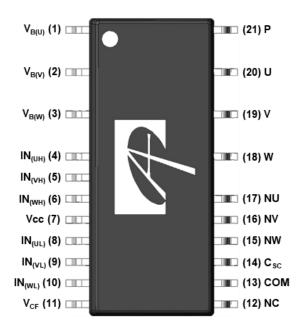
Applications

- AC 100~240Vrms class low power motor drives
- Refrigerators, Dishwashers, Drain Pumps and Fan Motors



Internal Equivalent Circuit / Pin Configuration







Ordering Information

Pa	rt Number	Package	Description
AIM7	DT1AR60V3	IPM-7DA	N/A



AOS Green Products use reduced levels of Halogens, and are also RoHS compliant.

 $Please\ visit\ \underline{https://aosmd.com/sites/default/files/media/AOSGreenPolicy.pdf}\ for\ additional\ information.$

Pin Description

Pin Number	Pin Name	Pin Function
1	$V_{B(U)}$	High-Side Bias Voltage for U-phase IGBT Driving
2	$V_{B(V)}$	High-Side Bias Voltage for V-phase IGBT Driving
3	$V_{B(W)}$	High-Side Bias Voltage for W-phase IGBT Driving
4	IN _(UH)	Signal Input for High-Side U-phase
5	IN _(VH)	Signal Input for High-Side V-phase
6	IN _(WH)	Signal Input for High-Side W-phase
7	Vcc	Control Supply Voltage
8	IN _(UL)	Signal Input for Low-Side U-phase
9	IN _(VL)	Signal Input for Low-Side V-phase
10	IN _(WL)	Signal Input for Low-Side W-phase
11	V _{CF}	Controllable Fault Output
12	NC	No connection
13	COM	Common Supply Ground
14	Csc	Capacitor (Low-Pass Filter) for Short-Circuit Current Detection Input
15	NW	Negative DC-Link Input for W-Phase
16	NV	Negative DC-Link Input for V-Phase
17	NU	Negative DC-Link Input for U-Phase
18	W	Output for W-phase
19	V	Output for V-phase
20	U	Output for U-phase
21	Р	Positive DC-Link Input

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Absolute Maximum Ratings (TJ=25°C, unless otherwise specified)

Symbol	Parameter	Conditions	Ratings	Units				
Inverter								
BV _{CES}	IGBT Breakdown Voltage	T _J =25°C	600	V				
Ic I	ICRT Callegater Comment (Continuous)	T _C =25°C	1	Α				
	IGBT Collector Current (Continuous)	T _C =80°C	0.5	Α				
I _{CP}	IGBT Collector Current (Pulsed)	T _C =25°C, <100µs pulse width	1.5	Α				
P _D	Maximum Power Dissipation	T _C =25°C	35.7	W				
TJ	Operating Junction Temperature		-40 to 150	°C				
Control (P	Control (Protection)							
Vcc	Control Supply Voltage	Applied between Vcc-COM	-0.3 ~ 20	V				
V _{BS}	High-Side Control Bias Voltage	Applied between V _{B(U)} -U, V _{B(V)} -V, V _{B(W)} -W	-0.3 ~ 20	V				
V _{IN}	Input Voltage	Applied between IN(UH), IN(VH), IN(WH), IN(UL), IN(VL), IN(WL)-COM	-0.3 ~ Vcc+0.5	V				
V _{CF}	Fault Output Supply Voltage	Applied between V _{CF} -COM	-0.3 ~ 5.5	V				
Thermal R	esistance							
R _{th(j-c)Q}	Investigate Cons. They would Desigt an ac-	Single RC-IGBT	2.8	°C/W				
R _{th(j-c)} F	Junction to Case Thermal Resistance	Single Diode	4	°C/W				
	Total System							
Tc	Module Case Operation Temperature		-30 to 125	°C				
T _{STG}	Storage Temperature		-40 to 150	°C				
Viso	Isolation Voltage	60Hz, sinusoidal, AC 1min, between connected all pins and heat sink plate	1500	V _{rms}				

Recommended Operation Conditions

Symbol	Parameter	Conditions	Min.	Тур.	Max	Units
V _{PN}	Bus Supply Voltage	Applied between P-N	0	300	450	V
Vcc	Control Supply Voltage	Applied between Vcc-COM	13.5	15.0	16.5	V
V _{BS}	High-Side Bias Voltage	Applied between V _{B(U)} -U, V _{B(V)} -V, V _{B(W)} -W	13.5	15.0	16.5	V
dV _{CC} /dt, dV _{BS} /dt	Control Supply Variation		-1	-	1	V/us
t _{dead}	Arm Shoot-Through Blocking Time	For each input signal	1.5	-	-	μs
fpwM	PWM Input Frequency	-40°C < T _J < 150°C	-	16	-	kHz
PW _{IN(ON)}	Minimum Input Pulse Width	(Note 1)	0.7	-	-	μs
PW _{IN(OFF)}	Willimidin input Pulse Width	(Note 1)	0.7	-	-	μs

Note:

1. IPM may not respond if the input pulse width is less than $PW_{IN(ON)}$, $PW_{IN(OFF)}$.

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Electrical Characteristics (T_J=25°C, unless otherwise specified)

Symbol	Parameter	Conditions		Min.	Тур.	Max	Units
Inverter		•			•	•	•
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	V _{CC} =V _{BS} =15V, V _{IN} =5V	I _C =1A	-	2.0	2.6	V
VF	Emitter-Collector Forward Voltage	V _{CC} =V _{BS} =15V, V _{IN} =0	Ic=1A	-	2.4	2.9	V
t _{OFF}				-	1000	-	ns
t_f		V _{PN} =300V, V _{CC} =V _{BS} =15V I _C =1A, V _{IN} =0V↔5V		-	90	-	ns
ton	Switching Times			-	600	-	ns
t _r		Inductive load (high-side)	-	50	-	ns	
t _{rr}	1			-	210	-	ns
Ices	Collector-Emitter Leakage Current	V _{IN} =0V, V _{CE} =600V		-	-	1	mA
Control (P	rotection)						
lacc	Quiescent Vcc Supply Current	V _{CC} =15V, IN _(UL, VL, WL) =0V	Vcc-COM	-	-	1.5	mA
I _{QBS}	Quiescent V _{BS} Supply Current	V _{BS} =15V, IN _(UH, VH, WH) =0V	$V_{B(U)}$ -U, $V_{B(V)}$ -V, $V_{B(W)}$ -W	-	-	0.3	mA
UVcct		Trip Level		10.3	11.4	12.5	V
UV_CCR	Supply Circuit Under- Voltage	Reset Level		10.8	11.9	13.0	V
UV_{BST}	Protection	Trip Level		9.0	10.0	11.0	V
UV_{BSR}		Reset Level	Reset Level		11.0	12.0	V
Vsc	Short-Circuit Trip Level	Vcc=15V	Vcc=15V		0.48	0.51	V
OT _T	Over-Temperature Protection	1 1/00-151/	Trip Level	110	130	150	°C
OTHYS	Over remperature reconstr		Hysteresis	-	30	-	°C
VcFH	Fault Output Voltage	V _N =0V		4.9	-	-	V
V _{CFL}		V _N =1V		-	-	0.5	V
V _{CF+}	CF positive going threshold			-	1.9	2.2	V
V _{CF} -	CF negative going threshold			0.8	1.1	-	V
t _{FO}	Fault Output Pulse Width (Note 2)			20	-	-	μs
I _{IN}	Input Current	V _{IN} =5V		-	650	-	μΑ
$V_{TH(ON)}$	ON Threshold Voltage	Applied between IN(UH), IN(VH), IN(WH),		-	-	2.5	V
V _{TH(OFF)}	OFF Threshold Voltage	IN _(UL) , IN _(VL) , IN _(WL) –COM		0.8	-	-	V
Bootstrap							
V _{F(BSD)}	Bootstrap Diode Forward Voltage	I _F =10mA including voltage drop by limiting resistor		-	3.6	-	V
R _{BSD}	Bootstrap Diode Equivalent Resistance			-	360	-	Ω

Note:

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^{2.} Fault output signal V_{CF} becomes low when one of protections OT, SC or UVLO is triggered. When failures happen like UV or OT, V_{CF} keeps low continuously until recovering from UV or OT state. 20µs indicates min. fault output duration time without pull-down capacitor. It can be controlled by the capacitor value as shown in Figure 1.



Functional Description

Controllable Fault Output Circuit

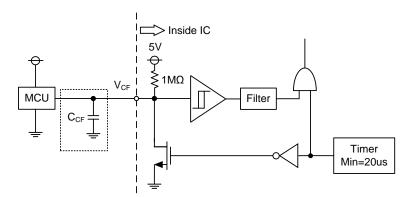


Figure 1. V_{CF} Output Circuit

 V_{CF} pin provides an enable functionality that enables to shut down all low side IGBTs, besides it can be controlled with external MCU. When V_{CF} is in the high state, the IPM is able to operate normally. Meanwhile, V_{CF} is in a low state, the low-side IGBTs are turned off until V_{CF} recovers to the high state. In addition, the V_{CF} pin provides fixed or adjustable pulse width of fault output signal using external capacitor. If V_{CF} pin is left, the fault output pulse width t_{FO} is maintained as the low state for minimum 20us. If a capacitor is connected, the pulse width can be increased depending on to the capacitance.

The pulse width can be determined by the following formula;

$$t_{FO} = -(1M\Omega \cdot C_{CF}) \cdot ln\left(1 - \frac{V_{CF+}}{5V}\right) + 20usec$$

$$\approx 478k \cdot C_{CF} + 20usec$$

for example, adding C_{CF}=1nF, t_{FO}≈500us.

Short-Circuit (SC) Protection and Time Chart

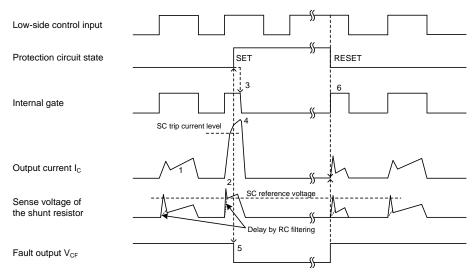


Figure 2. Short-Circuit Protection

(Low-side Operation Only with External Shunt Resistor and RC Filter)

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- (1) Normal operation: IGBT turns on and output current.
- (2) Short-circuit current detection (SC triggered).
- (3) All low-side IGBTs' gate are turned off.
- (4) Accordingly, all low-side IGBTs are turned off.
- (5) Fault signal outputs. F_O duration time (t_{FO}) is minimum 20 μ s.
- (6) Fault output finishes. Normal operation starts according to the input signal.

V_{CC} Under-voltage Lock-out (UVLO) Protection and Time Chart

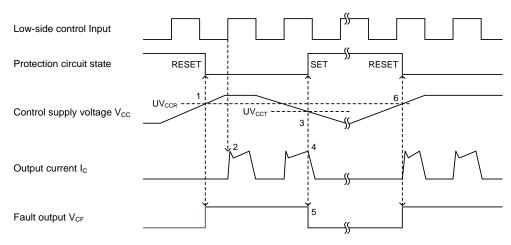


Figure 3. Under-Voltage Protection (Low-side, Vcc)

- (1) Supply voltage Vcc becomes higher than under-voltage reset level (UVccR), and IGBTs are turned at ON signal.
- (2) Normal operation: IGBTs turn-on and output current.
- (3) V_{CC} level drops to under-voltage trip level (UV_{CCT}).
- (4) All low-side IGBTs are turned off regardless of control input condition.
- (5) F_O output is generated, and F_O stays low as long as V_{CC} is below UV_{CCR} .
- (6) V_{CC} level reaches UV_{CCR}. Normal operation starts according to the input signal.

V_{BS} Under-voltage Lock-out (UVLO) Protection and Time Chart

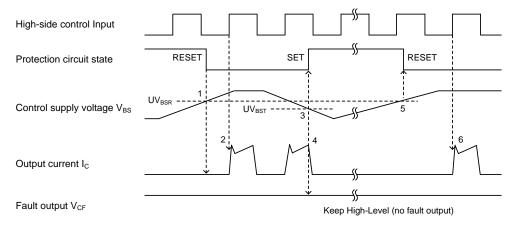


Figure 4. Under-Voltage Protection (High-side, V_{BS})

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- (1) Control supply voltage VBS rises. After the voltage reaches under-voltage reset level (UVBSR), IGBTs are turned on by the next ON signal.
- (2) Normal operation: IGBTs turn on and output current.
- (3) V_{BS} level drops to under-voltage trip level (UV_{BST}).
- (4) All high-side IGBTs are turned off regardless of control input condition.
- (5) V_{BS} level reaches UV_{BSR}.
- (6) Normal operation starts according to the input signal.

Over Temperature (OT) Protection and Time Chart

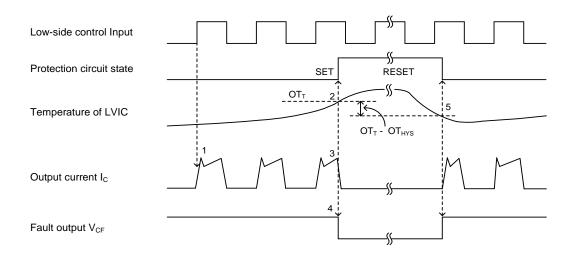


Figure 5. Over-Temperature Protection (Low-side, Detecting LVIC Temperature)

- (1) Normal operation: IGBTs turn on and output current.
- (2) LVIC temperature exceeds over-temperature trip level (OT_T).
- (3) All low-side IGBTs are turned off regardless of control input condition.
- (4) Fo output is generated, and Fo stays low as long as LVIC temperature is over OT_T.
- (5) LVIC temperature drops to over-temperature reset level (OT_T-OT_{HYS}). Normal operation starts according to the input signal.

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Switching Time Definition

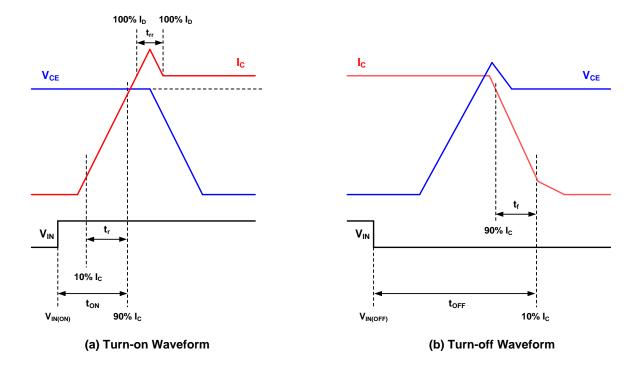
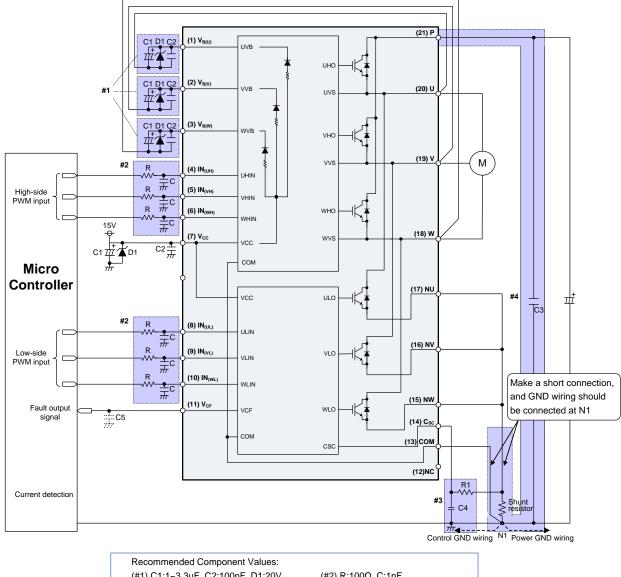


Figure 6. Switching Times Definition

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Example of Application Circuit



(#1) C1:1~3.3µF, C2:100nF, D1:20V

(#3) R1:1kΩ, C4:2nF

(#2) R:100Ω, C:1nF

(#4) C3:0.1~0.22µF

- If the control GND is connected with the power GND by common broad pattern, it may cause malfunction by power GND fluctuation. It is recommended to connect the control GND and power GND at a point (N1), near the terminal of shunt resistor.
- A zener diode D1 (20V/1W) is recommended between each pair of control supply pins to prevent surge destruction.
- Prevention of surge destruction can further be improved by placing the bus capacitor as close to pin P and N1 as possible. Generally a 0.1~0.22µF snubber capacitor C3 between the P-N1 terminals is recommended.
- (4) Selection of the R1*C4 filter components for short-circuit protection is recommended to have tight tolerance, and is temperaturecompensated type. The R1*C4 time constant should be set such that SC current is shut down within 2µs; (typically 1.5-2µs). R1 and C4 should be placed as close as possible to the Csc pin. SC interrupting time may vary with layout patterns and components selections, therefore thorough evaluation in the system is necessary.
- It is recommended that all capacitors are mounted as close to the IPM as possible. (C1: electrolytic type with good temperature and frequency characteristics. C2: ceramic type with 0.1µF, good temperature, frequency and DC bias characteristics).
- To prevent malfunction, the layout to each input should be as short as possible. When using the RC coupling circuit (R: 100Ω, C: 1nF), place it as close to the IPM input pins as possible, and make sure the input signal levels meet the required turn-on and turn-off threshold voltages.
- The V_{CF} pin can provide the fault output signal with the fixed or adjustable pulse width. If the V_{CF} pin is left, the pulse width is fixed at minimum 20us. If a capacitor C5 is connected, the pulse width can be adjusted according to the capacitor value. For the design guide, please refer to the Figure 1.

DIMENSION IN INCHS

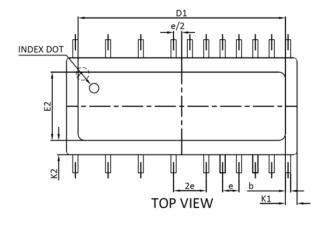
NOM.

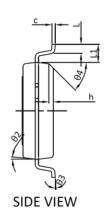
0.015TYP.

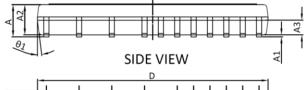
MAX.

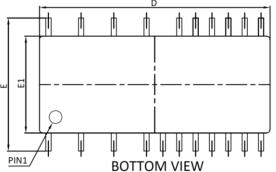


Package Dimensions, IPM-7DA









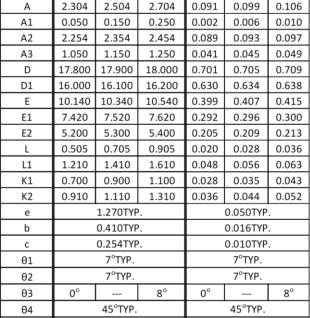


SYMBOLS

MIN.

LAND PATTERN RECOMMENDATIONS

9.620



MAX.

MIN.

DIMENSION IN MILLIMETRES

NOM.

0.381TYP.

UNIT: mm

h

NOTES

- 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS, MOLD FLASH SHOULD BE LESS THAN 6 MIL.
- 2. TOLERANCE 0.100 MILLIMETERS UNLESS OTHERWISE SPECIFIED.
- 3. CONTROLLING DIMENSION IS MILLIMETER, CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

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